

Vishay Siliconix

### 16 $\Omega$ , Low Parasitic Capacitance and Leakage, +12 V / +5 V / +3 V / ± 5 V Quad SPST Switches

#### DESCRIPTION

The DG411LE, DG412LE, and DG413LE are monolithic quad single-pole-single-throw analog switches. The DG411LE and DG412LE differ only in that they respond to opposite logic levels. The DG413LE has two normally open and two normally closed switches. It can be given various configurations, including four SPST, two SPDT, and one DPDT.

The DG411LE, DG412LE, and DG413LE offer low on resistance of 16  $\Omega$ , low parasitic capacitance of 15 pF switch on capacitance, and low charge injection over the signal swing range.

The DG411LE, DG412LE, and DG413LE operate on single and dual supplies. Single supply voltage ranges from 3 V to 16 V while dual supply operation is recommended with  $\pm$  3 V to  $\pm$  8 V. Each switch conducts equally well in both direction when on, and blocks input voltages up to the supply levels when off.

The DG411LE, DG412LE, and DG413LE are available in 16 lead TSSOP, SOIC, and PDIP packages.

#### FEATURES

- 3 V to 16 V single supply or  $\pm$  3 V to  $\pm$  8 V dual supply
- On-resistance  $R_{DS(on)}$ : 16  $\Omega$
- Low parasitic capacitance: C<sub>D(ON)</sub>: 15 pF C<sub>S(OFF)</sub>: 5 pF
- Less than 8 pC charge injection over the full signal swing range
- Fast switching t<sub>ON</sub>: 16 ns t<sub>OFF</sub>: 9 ns
- TTL, CMOS compatible
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

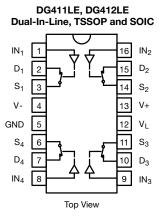
#### BENEFITS

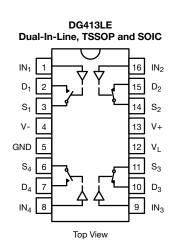
- Wide operation voltage range
- · Low signal errors and distortion
- Fast switching time
- Minimized switching glitch

#### APPLICATIONS

- Automatic test equipment
- · Data acquisition systems
- Meters and instruments
- · Medical and healthcare systems
- Communication systems
- Audio and video signal routing
- Relay replacement
- Battery powered systems
- Computer peripherals
- · Audio and video signal routing

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





S19-0672-Rev. B, 05-Aug-2019

1 For technical questions, contact: <u>analogswitchsupport@vishay.com</u> Document Number: 78091

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### **Vishay Siliconix**

TRUTH TABLE	

LOGIC	DG411LE	DG412LE				
0	ON	OFF				
1	OFF	ON				
$l_{action} "0" < 0.9 V$	•					

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

TRUTH TABLE						
LOGIC	SW <sub>1</sub> , SW <sub>4</sub>	SW <sub>2</sub> , SW <sub>3</sub>				
0	OFF	ON				
1	ON	OFF				

Logic "0"  $\leq$  0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION								
TEMP. RANGE	CONFIGURATION	PACKAGE	PART NUMBER	MIN. ORDER / PACK. QUANTITY				
		16-pin TSSOP	DG411LEDQ-GE3	Tube 360 units				
		10-pill 1330P	DG411LEDQ-T1-GE3	Tape and reel, 3000 units				
	DG411LE	16-pin SOIC	DG411LEDY-GE3	Tube 500 units				
		10-pin 3010	DG411LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG411LEDJ-GE3	Tube 500 units				
	DG412LE	16-pin TSSOP	DG412LEDQ-GE3	Tube 360 units				
40.00 1 05.00			DG412LEDQ-T1-GE3	Tape and reel, 3000 units				
-40 °C to +85 °C Lead-free		16-pin SOIC	DG412LEDY-GE3	Tube 500 units				
			DG412LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG412LEDJ-GE3	Tube 500 units				
		16-pin TSSOP	DG413LEDQ-GE3	Tube 360 units				
		10-pill 1330P	DG413LEDQ-T1-GE3	Tape and reel, 3000 units				
	DG413LE	16-pin SOIC	DG413LEDY-GE3	Tube 500 units				
		10-pin 3010	DG413LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG413LEDJ-GE3	Tube 500 units				

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		LIMIT	UNIT			
V+ to V-		-0.3 to +18				
GND to V-		18				
VL		(GND -0.3) to (V+) +0.3	V			
I <sub>N</sub> <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		-0.3 to (V+) +0.3 or 30 mA, whichever occurs first				
Continuous Current (Any terminal)		30				
Peak Current, S or D (Pulsed 1 ms, 10 % du	ity cycle)	100	- mA			
Storogo Tomporaturo	(DQ, DY suffix)	-65 to +125	°C			
Storage Temperature	(AK suffix)	-65 to +150	U			
	16-pin TSSOP °	450				
Power Dissipation (Packages) <sup>b</sup>	16-pin SOIC <sup>d</sup>	650	mW			
	16-pin CerDIP <sup>e</sup>	900				
ESD Human Body Model (HBM); per ANSI /	ESDA / JEDEC® JS-001	2500	V			
Latch Up Current, per JESD78D		400	mA			

Notes

- a. Signals on S<sub>X</sub>, D<sub>X</sub>, or IN<sub>X</sub> exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings b. All leads welded or soldered to PC board
- c. Derate 7 mW/°C above 75 °C

d. Derate 7.6 mW/°C above 75 °C

e. Derate 12 mW/°C above 75 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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# DG411LE, DG412LE, DG413LE

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SPECIFICATIONS <sup>a</sup> (Single Supply 12 V)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TYP. °	A SUFFIX LIMITS -55 °C to +125 °C		LIM	IFFIX IITS o +85 °C	UNIT
		V+ = 12 V, V- = 0 V V <sub>L</sub> = 5 V, V <sub>IN</sub> = 2.4 V, 0.8 V <sup>f</sup>			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch									
Analog Signal Range <sup>e</sup>	VANALOG		Full	-	0	12	0	12	V
Drain-Source	R <sub>DS(on)</sub>	V+ = 10.8 V, V- = 0 V	Room	16	-	26	-	26	Ω
On-Resistance	US(on)	$I_{\rm S}$ = 10 mA, $V_{\rm D}$ = 2/9 V	Full	-	-	40	-	35	22
	la cura		Room	-	-1	1	-1	1	
Switch Off Leakage Current	I <sub>S(off)</sub>	V <sub>D</sub> = 1/11 V, V <sub>S</sub> = 11/1 V	Full	-	-15	15	-10	10	
Switch On Leakage Ourient	1	$v_{\rm D} = 1/11$ v, $v_{\rm S} = 1/11$ v	Room	-	-1	1	-1	1	nA
	I <sub>D(off)</sub>		Full	-	-15	15	-10	10	ПА
Channel On Leakage		$V_{\rm S} = V_{\rm D} = 11/1 \ {\rm V}$	Room	-	-1	1	-1	1	
Current	I <sub>D(on)</sub>		Full	-	-15	15	-10	10	
Digital Control									
Input Current, VIN Low	IIL	V <sub>IN</sub> under test = 0.8 V	Full	0.01	-1.5	1.5	-1	1	μA
Input Current, VIN High	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full		-1.5	1.5	-1	1	μA
Dynamic Characteristics									
Turn-On Time	tou	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF,	Room	16	-	50	-	50	ns
	t <sub>ON</sub>		Full	-	-	70	-	60	
Turn-Off Time	+	$V_{\rm S}$ = 5 V, see figure 2	Room	9	-	30	-	30	
	t <sub>OFF</sub>		Full	-	-	48	-	40	
Break-Before-Make Time Delay	t <sub>D</sub>	DG413L only, $V_S = 5 V$ , $R_L = 300 \Omega$ , CL = 35 pF	Room	5	-	-	-	-	
Charge Injection <sup>e</sup>	Q	$V_g = 0 V, R_g = 0 \Omega, C_L = 10 nF$	Room	6.6	-	-	-	-	рС
Off-Isolation <sup>e</sup>	OIRR		Room	68.4	-	-	-	-	
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 1 MHz	Room	114	-	-	-	-	dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	5	-	-	-	-	
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	6	-	-	-	-	pF
Channel-On Capacitance e	C <sub>D(on)</sub>		Room	15	-	-	-	-	
Power Supplies	•	•					•		
Desitive Supply Current	I+		Room	0.02	-	1	-	1	
Positive Supply Current	1+		Full	-	-	7.5	-	5	
Negative Supply Current	I-	]	Room	-0.002	-1	-	-1	-	
Negative Supply Current	1-		Full	-	-7.5	-	-5	-	1 .
Logio Supply Ormant		V <sub>IN</sub> = 0 V or 5 V	Room	0.002	-	1	-	1	μA
Logic Supply Current	۱L		Full	-	-	7.5	-	5	1
Cround Current		1	Room	-0.002	-1	-	-1	-	
Ground Current	I <sub>GND</sub>		Full	-	-7.5	-	-5	-	

Notes

a. Refer to PROCESS OPTION FLOWCHART

b. Room = 25 °C, full = as determined by the operating temperature suffix

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

e. Guaranteed by design, not subject to production test

f. V<sub>IN</sub> = input voltage to perform proper function

g. Leakage parameters are guaranteed by worst case test conditions and not subject to test

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SPECIFICATIONS <sup>a</sup> (Dual Supply ± 5 V)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TYP. °	A SUFFIX LIMITS -55 °C to +125 °C		LIN	<b>JFFIX</b> IITS o +85 °C	UNIT
		V+ = 5 V, V- = -5 V V <sub>L</sub> = 5 V, V <sub>IN</sub> = 2.4 V, 0.8 V <sup>f</sup>			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch									•
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	-5	5	-5	5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V+ = 5 V, V- = -5 V, I <sub>S</sub> = 10 mA, V <sub>D</sub> = ± 3.5 V	Room Full	18	-	30 42	-	30 37	Ω
			Room	-	-1	42	-1	1	
Quittab Off	I <sub>S(off)</sub>		Full	_	-15	15	-10	10	-
Switch Off Leakage Current <sup>g</sup>		V+ = 5.5, V- = -5.5 V, V <sub>D</sub> = ± 4.5 V, V <sub>S</sub> = ± 4.5 V	Room	-	-1	1	-1	1	-
	I <sub>D(off)</sub>		Full	-	-15	15	-10	10	nA
Channel On		V+ = 5.5 V, V- = -5.5 V,	Room	-	-1	1	-1	1	
Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	$V_{\rm S} = V_{\rm D} = \pm 4.5 \text{ V}$	Full	-	-15	15	-10	10	
Digital Control									
Input Current, V <sub>IN</sub> Low <sup>e</sup>	IIL.	V <sub>IN</sub> under test = 0.8 V	Full	0.05	-1.5	1.5	-1	1	
Input Current, V <sub>IN</sub> High <sup>e</sup>	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.05	-1.5	1.5	-1	1	μA
Dynamic Characteristics						1			
T O . T o			Room	17	-	50	-	50	
Turn-On Time <sup>e</sup>	t <sub>ON</sub>	$R_1 = 300 \Omega, C_1 = 35 pF,$	Full	-	-	70	-	60	ns
<b>T</b> 0// <b>T</b> 0		$V_{S} = \pm 3.5 V$ , see figure 2	Room	12	-	35	-	35	
Turn-Off Time <sup>e</sup>	t <sub>OFF</sub>		Full	-	-	50	-	40	115
Break-Before-Make Time Delay <sup>e</sup>	t <sub>D</sub>	DG413L only, $V_S = 3.5 V$ , R <sub>L</sub> = 300 $\Omega$ , C <sub>L</sub> = 35 pF	Room	5	-	-	-	-	
Charge Injection <sup>e</sup>	Q	$V_g = 0 V, R_g = 0 \Omega, C_L = 10 nF$	Room	5.8	-	-	-	-	рС
Off Isolation <sup>e</sup>	OIRR		Room	68	-	-	-	-	
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 $ Ω, $C_L = 5 $ pF, f = 1 MHz	Room	113	-	-	-	-	dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	5	-	-	-	-	
Drain Off Capacitance e	C <sub>D(off)</sub>	f = 1 MHz	Room	6	-	-	-	-	pF
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	14	-	-	-	-	
Power Supplies									
Positive Supply Current <sup>e</sup>	l+		Room	0.03	-	1	-	1	
	1+		Full	-	-	7.5	-	5	
Negative Supply Current <sup>e</sup>	-		Room	-0.002	-1	-	-1	-	
Regarive Supply Surrent	1-	V <sub>IN</sub> = 0 V or 5 V	Full	-	-7.5	-	-5	-	μA
Logic Supply Current <sup>e</sup>	ΙL		Room	0.002	-	1	-	1	μΛ
	'L		Full	-	-	7.5	-	5	
Ground Current <sup>e</sup>	I <sub>GND</sub>		Room	-0.002	-1	-	-1	-	
	GND		Full	-	-7.5	-	-5	-	

Notes

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d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

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f. V<sub>IN</sub> = input voltage to perform proper function

g. Leakage parameters are guaranteed by worst case test conditions and not subject to test

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**Vishay Siliconix** 

<b>SPECIFICATIONS</b> <sup>a</sup>	SPECIFICATIONS <sup>a</sup> (Single Supply 5 V)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TYP. °	A SUFFIX LIMITS -55 °C to +125 °C		D SUFFIX LIMITS -40 °C to +85 °C		UNIT
		V+=5 V, V-=0 V $V_{L}=5 V, V_{IN}=2.4 V, 0.8 V f$			MIN. <sup>d</sup>	MAX. d	MIN. d	MAX. d	
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	-	-	5	-	5	V
Drain-Source	R <sub>DS(on)</sub>	V+ = 4.5 V,	Room	36	-	50	-	50	Ω
On-Resistance e	US(on)	$I_{S} = 5 \text{ mA}, V_{D} = 1 \text{ V}, 3.5 \text{ V}$	Full	-	-	88	-	75	32
Dynamic Characteristics									
Turn-On Time <sup>e</sup>	t <sub>ON</sub>		Room	27	-	50	-	50	
	UN	$R_L = 300 \Omega, C_L = 35 pF,$ V <sub>S</sub> = 3.5 V, see figure 2	Hot	-	-	90	-	60	ns
Turn-Off Time <sup>e</sup>	torr		Room	15	-	30	-	30	
	OFF		Hot	-	-	55	-	40	-
Break-Before-Make Time Delay <sup>e</sup>	t <sub>D</sub>	DG413L only, $V_S$ = 3.5 V, R <sub>L</sub> = 300 $\Omega$ , C <sub>L</sub> = 35 pF	Room	11	-	-	-	-	
Charge Injection <sup>e</sup>	Q	$V_g = 0 V, R_g = 0 \Omega, C_L = 10 nF$	Room	3.3	-	-	-	-	рС
Power Supplies									
Positive Supply Current <sup>e</sup>	I+		Room	0.02	-	1	-	1	
Positive Supply Current	1+		Hot	-	-	7.5	-	5	
Negative Supply Current e	-		Room	-0.002	-1	-	-1	-	
Negative Supply Current	1-	V <sub>IN</sub> = 0 V or 5 V	Hot	-	-7.5	-	-5	-	μA
Logic Supply Current <sup>e</sup>	١L	v <sub>IN</sub> = 0 v 0i 3 v	Room	0.002	-	1	-	1	μΑ
	١L		Hot	-	-	7.5	-	5	
Ground Current <sup>e</sup>	lour		Room	-0.002	-1	-	-1	-	
	I <sub>GND</sub>		Hot	-	-7.5	-	-5	-	

#### Notes

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d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

e. Guaranteed by design, not subject to production test

f.  $V_{IN}$  = input voltage to perform proper function

g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



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# DG411LE, DG412LE, DG413LE

**Vishay Siliconix** 

SPECIFICATIONS <sup>a</sup>	SPECIFICATIONS <sup>a</sup> (Single Supply 3 V)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. <sup>b</sup>	TEMP. <sup>b</sup> TYP. <sup>c</sup>	ASUFFIX LIMITS -55 °C to +125 °C		D SUFFIX LIMITS -40 °C to +85 °C		UNIT
		V+ = 3 V, V- = 0 V $V_L = 3 V, V_{IN} = 0.4 V, 2.0 V^{f}$			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch	•			•	•				
Analog Signal Range <sup>e</sup>	VANALOG		Full	-	0	3	0	3	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V+ = 2.7 V, V- = 0 V, I <sub>S</sub> = 5 mA, V <sub>D</sub> = 0.5, 2.2 V	Room Full	106	-	130 150	-	130 140	Ω
			Room	_	-1	1	-1	1	
Switch Off	I <sub>S(off)</sub>	V+ = 3.3, V- = 0 V,	Full	-	-15	15	-10	10	
Leakage Current <sup>g</sup>		$V_{\rm D} = 1, 2 \text{ V}, V_{\rm S} = 2, 1 \text{ V}$	Room	-	-1	1	-1	1	
	I <sub>D(off)</sub>		Full	-	-15	15	-10	10	nA
Channel On		V+ = 3.3 V, V- = 0 V,	Room	-	-1	1	-1	1	
Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	$V_{\rm S} = V_{\rm D} = 1, 2  {\rm V}$	Full	-	-15	15	-10	10	
Digital Control	•								
Input Current, V <sub>IN</sub> Low	۱ <sub>IL</sub>	$V_{IN}$ under test = 0.4 V	Full	0.005	-1.5	1.5	-1	1	μA
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.005	-1.5	1.5	-1	1	μΑ
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>		Room	57	-	85	-	85	
	UN	$R_L = 300 \ \Omega, \ C_L = 35 \ pF,$	Full	-	-	150	-	110	
Turn-Off Time	t <sub>OFF</sub>	$V_{\rm S}$ = 1.5 V, see figure 2	Room	25	-	60	-	60	ns
	•OFF		Full	-	-	100	-	85	
Break-Before-Make Time Delay	t <sub>D</sub>	DG413L only, $V_S = 1.5 V$ , R <sub>L</sub> = 300 $\Omega$ , C <sub>L</sub> = 35 pF	Room	24	-	-	-	-	
Charge Injection <sup>e</sup>	Q	$V_g = 0 V, R_g = 0 \Omega, C_L = 10 nF$	Room	2	-	-	-	-	рС
Off Isolation <sup>e</sup>	OIRR		Room	68	-	-	-	-	
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$	Room	107	-	-	-	-	dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	6	-	-	-	-	
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	7	-	-	-	-	pF
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	15	-	-	-	-	

Notes

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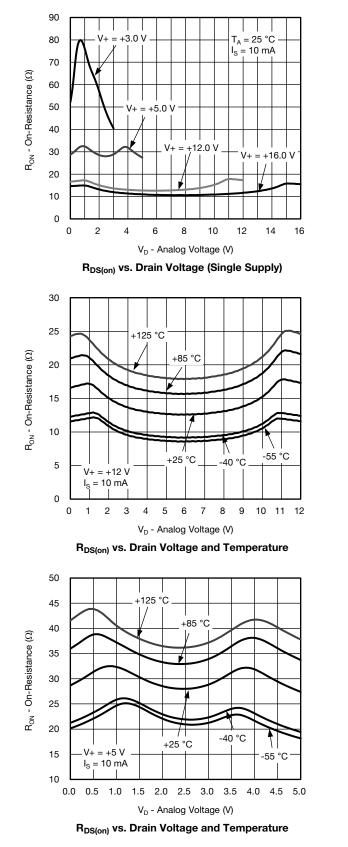
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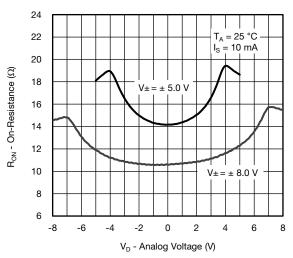
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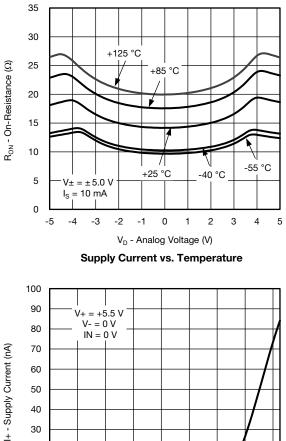
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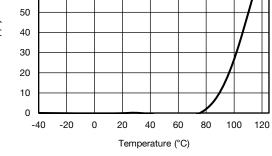
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





R<sub>DS(on)</sub> vs. Drain Voltage and Temperature (Single Supply)





Switching Time vs. Single Supply

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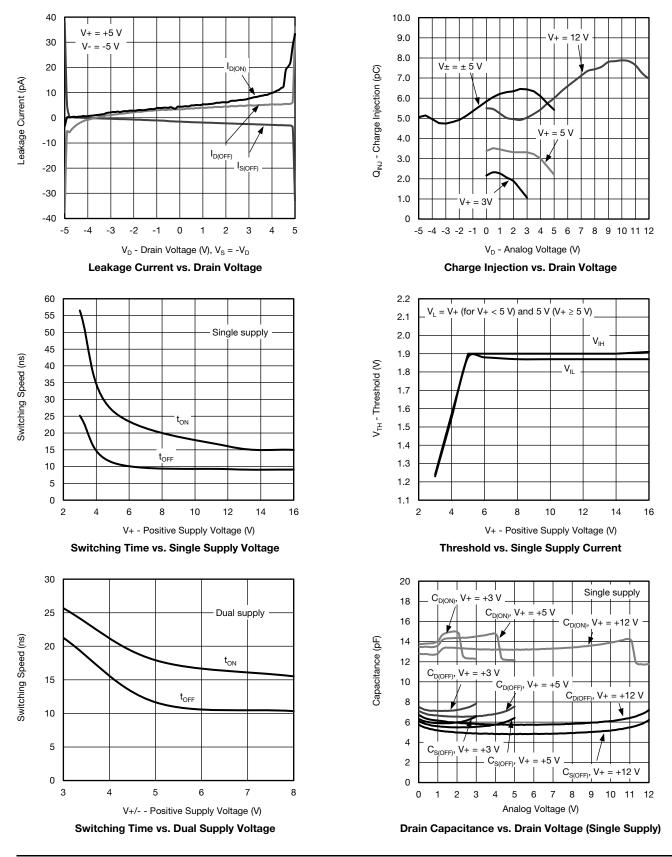
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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



S19-0672-Rev. B, 05-Aug-2019

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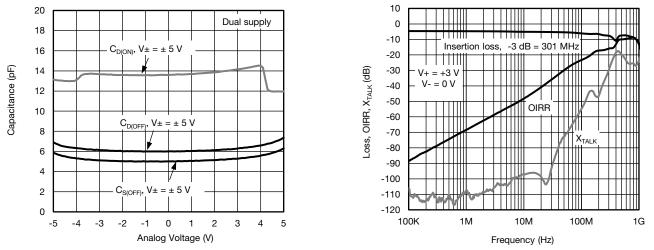
Document Number: 78091

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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Drain Capacitance vs. Drain Voltage (Dual Supply)

Insertion Loss, Off Isolation and Crosstalk vs. Frequency

#### SCHEMATIC DIAGRAM (Typical Channel)

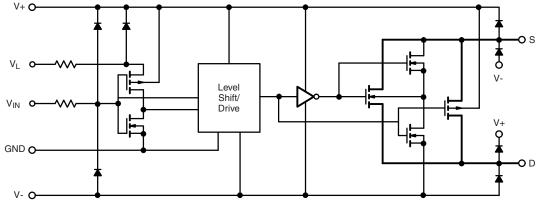


Fig. 1

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Rg

3 V

Vg

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C<sub>L</sub> (includes fixture and stray capacitance) Fig. 3 - Break-Before-Make (DG413LE)  $V_{\mathsf{L}}$ V+

> 0  $V_{O}$

C<sub>L</sub> 10 nF

Vo

IN<sub>X</sub>

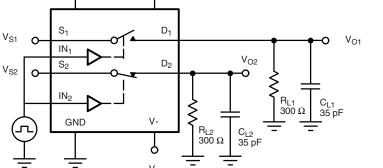
IN<sub>X</sub>

OFF

OFF

IN<sub>X</sub> dependent on switch configuration Input polarity determined

### Fig. 2 - Switching Time



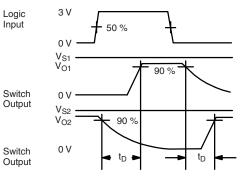
Q

V+

V-

P V-

D

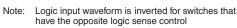


ON

ON

 $Q = \Delta V_O \times C_L$ 

3 V t<sub>r</sub> < 20 ns Logic Input t<sub>f</sub> < 20 ns 50% 0 V ton Switch Input\* ٧s Vo 90 % 0 V Switch Output ton 90 % V<sub>O</sub> V<sub>S</sub> Switch Input\*



# DG411LE, DG412LE, DG413LE

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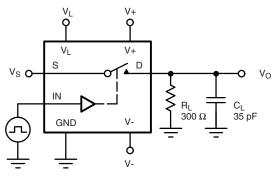
VL

Q

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#### **TEST CIRCUITS**

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CL (includes fixture and stray capacitance)



V+

Q

V-

Q

 $V_{\mathsf{L}}$ 

S

IN

GND



by sense of switch. Fig. 4 - Charge Injection

 $\Delta V_O$ 

OFF

OFF





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#### **TEST CIRCUITS**

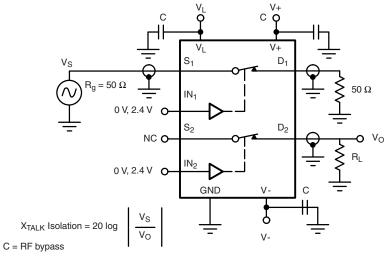
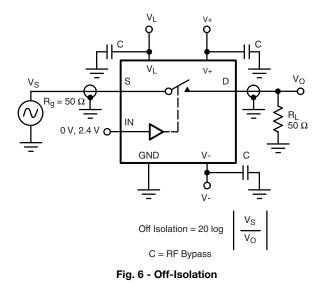


Fig. 5 - Crosstalk



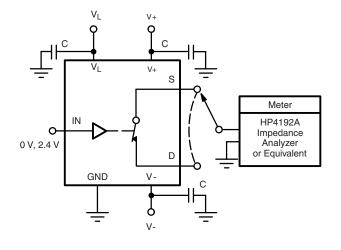


Fig. 7 - Source / Drain Capacitances

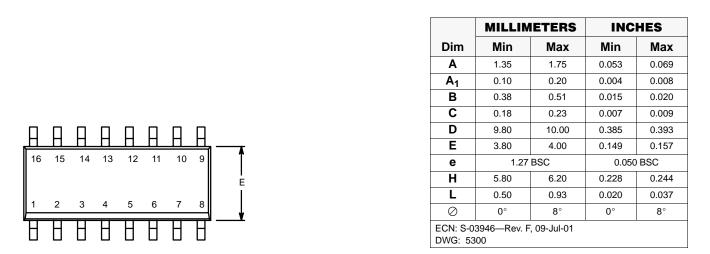
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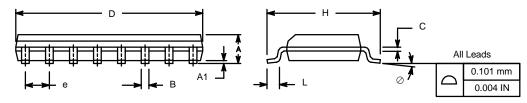


### Package Information Vishay Siliconix

SOIC (NARROW): 16-LEAD

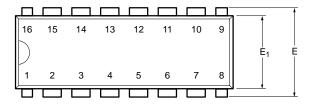
JEDEC Part Number: MS-012

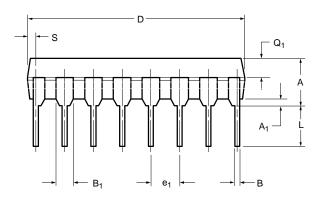


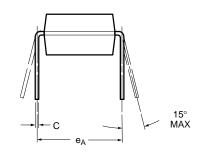




#### PDIP: 16-LEAD







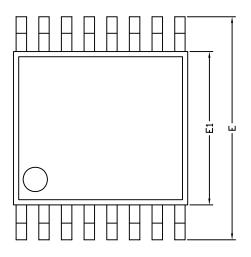
	MILLIN	IETERS	INC	HES			
Dim	Min	Max	Min	Max			
Α	3.81	5.08	0.150	0.200			
A <sub>1</sub>	0.38	1.27	0.015	0.050			
В	0.38	0.51	0.015	0.020			
B <sub>1</sub>	0.89	1.65	0.035	0.065			
С	0.20	0.30	0.008	0.012			
D	18.93	21.33	0.745	0.840			
E	7.62	8.26	0.300	0.325			
E <sub>1</sub>	5.59	7.11	0.220	0.280			
e <sub>1</sub>	2.29	2.79	0.090	0.110			
e <sub>A</sub>	7.37	7.87	0.290	0.310			
L	2.79	3.81	0.110	0.150			
<b>Q</b> 1	1.27	2.03	0.050	0.080			
S	0.38	1.52	.015	0.060			
	ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482						

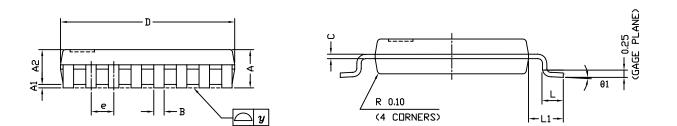


# Package Information

Vishay Siliconix

#### TSSOP: 16-LEAD





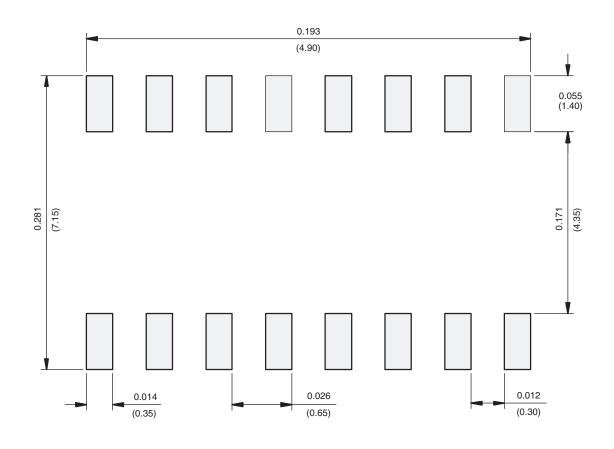
	C	DIMENSIONS IN MILLIMETERS					
Symbols	Min	Nom	Max				
A	-	1.10	1.20				
A1	0.05	0.10	0.15				
A2	-	1.00	1.05				
В	0.22	0.28	0.38				
С	-	0.127	-				
D	4.90	5.00	5.10				
E	6.10	6.40	6.70				
E1	4.30	4.40	4.50				
е	-	0.65	-				
L	0.50	0.60	0.70				
L1	0.90	1.00	1.10				
у	-	-	0.10				
θ1	0°	3°	6°				
ECN: S-61920-Rev. D, 23 DWG: 5624	-Oct-06						



**PAD** Pattern

Vishay Siliconix

#### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



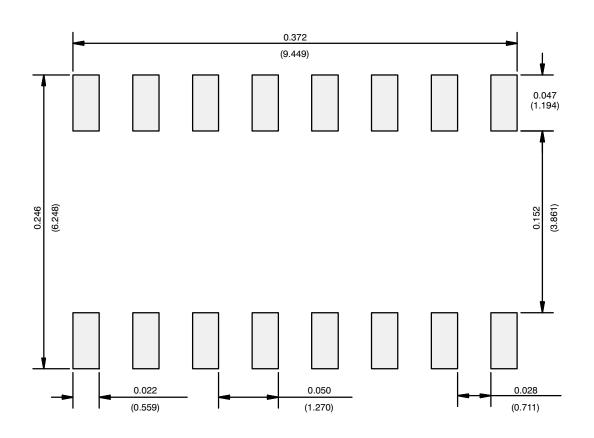
Recommended Minimum Pads Dimensions in inches (mm)

# **Application Note 826**

Vishay Siliconix



#### **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

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